

## DESCRIPTION

The MXN06P02 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

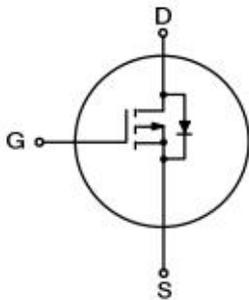
## GENERAL FEATURES

- $V_{DS}=-20V$ ,  $I_D=-60A$   
 $R_{DS(ON)}(Typ.)=7.5m\Omega$  @  $V_{GS}=-4.5V$   
 $R_{DS(ON)}(Typ.)=9.2m\Omega$  @  $V_{GS}=-2.5V$   
 $R_{DS(ON)}(Typ.)=12.3m\Omega$  @  $V_{GS}=-1.8V$
- Low Thermal Resistance
- Advanced trench cell design

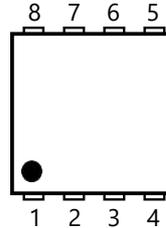
## APPLICATION

- Motor drivers
- DC-DC Converter

## PINOUT



Schematic diagram



PDFN3.3X3.3-8L Top View

Pin	Description
1,2,3	Source
4	Gate
5,6,7,8	Drain

## ORDERING INFORMATION

Part Number	Storage Temperature	Package	Devices Per Reel
MXN06P02	-55°C to 150°C	PDFN3.3X3.3	5000

## ABSOLUTE MAXIMUM RATINGS ( $T_C=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current ( $V_{GS}=-4.5V$ ) <sup>(Note1)</sup>	$I_D$	-60	A
Pulsed Source Current ( $V_{GS}=-4.5V$ ) <sup>(Note1)(Note2)(Note3)</sup>	$I_{DM}$	-96	A
Diode Forward Current	$I_S$	-60	A
Total Power Dissipation <sup>(Note1)</sup>	$P_{tot}$	20	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	°C
Thermal Resistance, Junction-to-Case <sup>(Note1)</sup>	$R_{\theta JC}$	6	°C/W

Note 1. Surface Mounted on 1 in<sup>2</sup> pad area,  $t \leq 10$  sec

Note 2. Pulse width  $\leq 10\mu s$ , duty cycle  $\leq 1\%$

Note 3. limited by bonding wire



**ELECTRICAL CHARACTERISTICS**( $T_C=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-16V, V_{GS}=0V$	-	-	-10	$\mu A$
		$V_{DS}=-16V, V_{GS}=0V, T_J=85^\circ C$	-	-	-30	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.3	-	-1.2	V
Drain-Source On-State Resistance <sup>(Note1)</sup>	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-20A$	-	7.5	9	m $\Omega$
		$V_{GS}=-2.5V, I_D=-15A$	-	9.2	12	
		$V_{GS}=-1.8V, I_D=-12A$	-	12.3	16	m $\Omega$
<b>Dynamic Characteristics<sup>(Note2)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-10V, V_{GS}=0V, F=1.0MHz$	-	5200	-	pF
Output Capacitance	$C_{oss}$		-	700	-	pF
Reverse Transfer Capacitance	$C_{rss}$		-	380	-	pF
<b>Switching Characteristics<sup>(Note2)</sup></b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=-10V, I_D=-1A, V_{GEN}=-5V, R_G=3.3\Omega$	-	27	-	nS
Turn-on Rise Time	$t_r$		-	21	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	240	-	nS
Turn-Off Fall Time	$t_f$		-	110	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=-10V, I_{DS}=-10A, V_{GS}=-4.5V$	-	60	-	nC
Gate-Source Charge	$Q_{gs}$		-	10	-	nC
Gate-Drain Charge	$Q_{gd}$		-	13.5	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note1)</sup>	$V_{SD}$	$V_{GS}=0V, I_{SD}=-2.6A$	-	-	-1.2	V
Reverse Recovery Time	$t_{rr}$	$I_{SD}=-10A, dl_{SD}/dt=100A/\mu s$	-	36	-	nS
Reverse Recovery Charge	$Q_{rr}$		-	20	-	nC

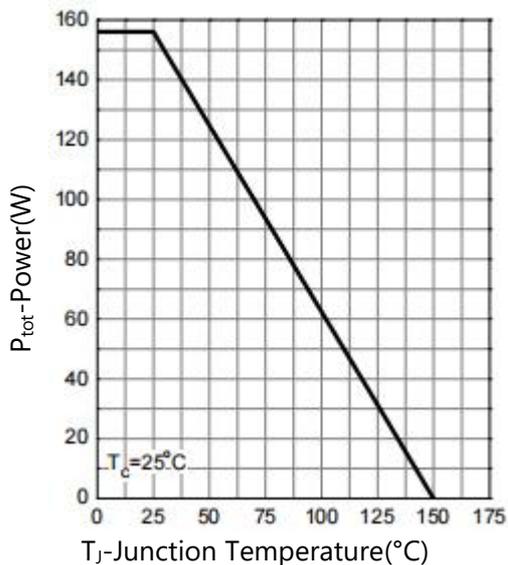
Note 1. The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$

Note 2. Guaranteed by design, not subject to production testing

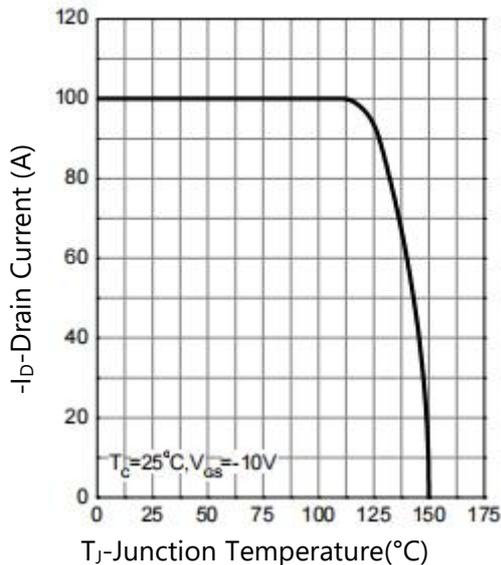


**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

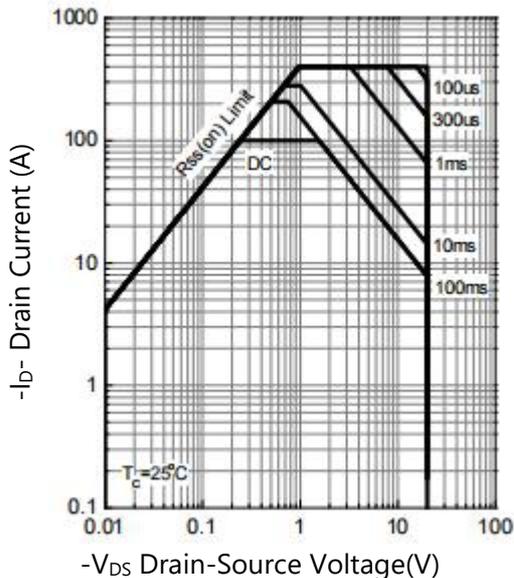
**Figure 1. Power Capability**



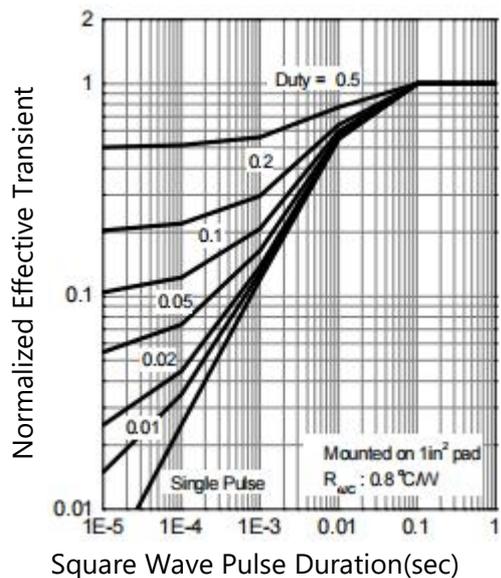
**Figure 2. Current Capability**



**Figure 3. Safe Operation Area**



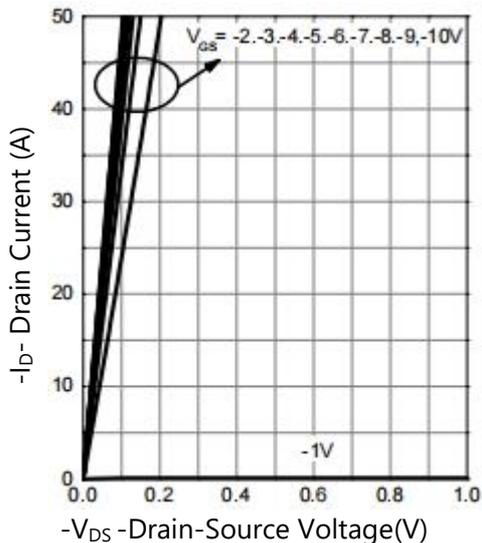
**Figure 4. Transient Thermal Impedance**



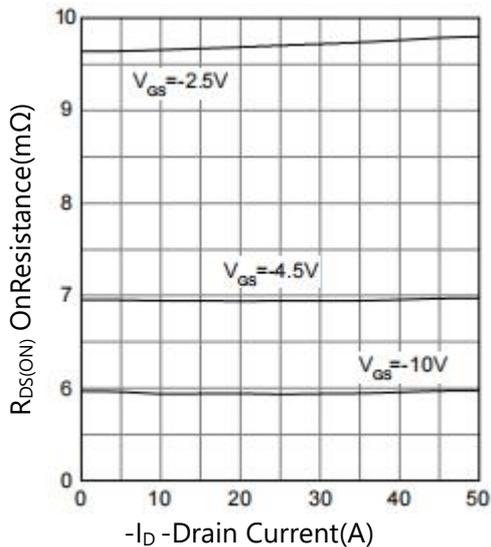


**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

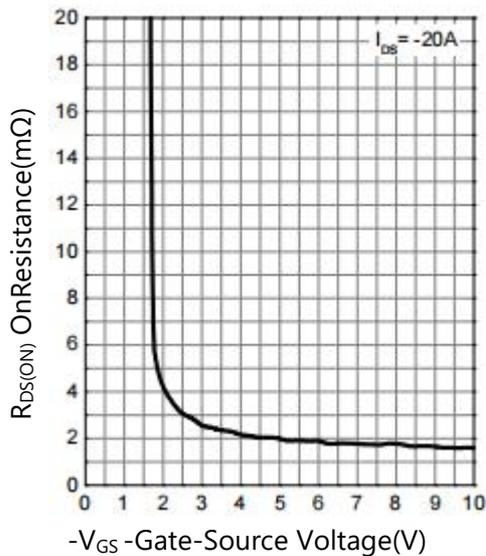
**Figure 5. Output Characteristics**



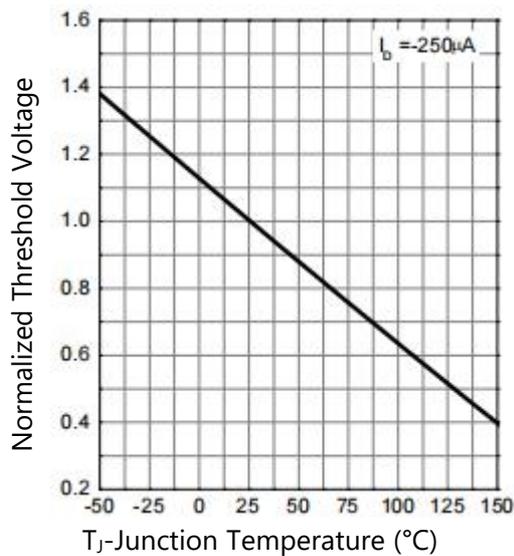
**Figure 6. Drain-Source On Resistance**



**Figure 7. Transfer Characteristics**



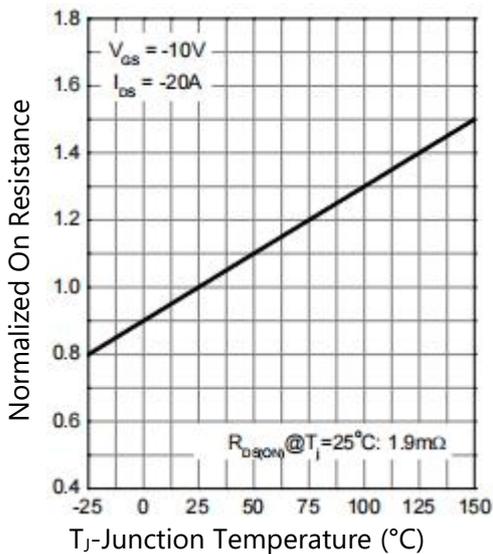
**Figure 8. Normalized Threshold Voltage**



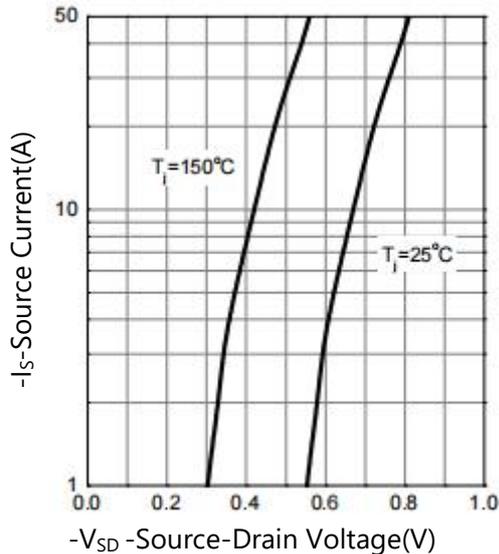


**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

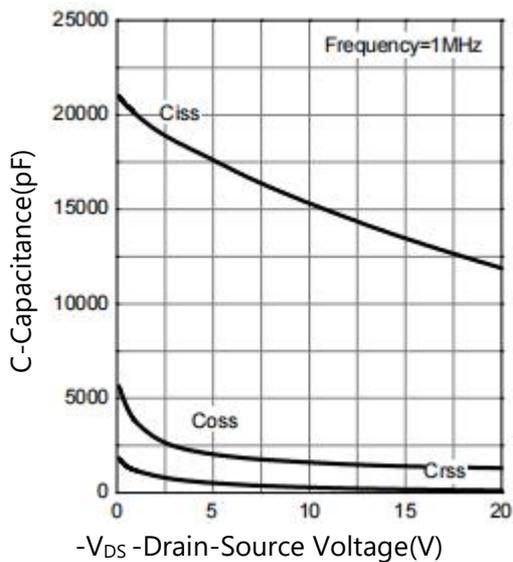
**Figure 9. Normalized On Resistance**



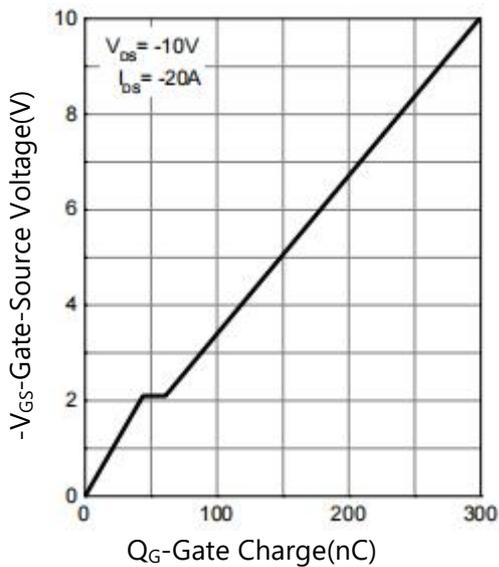
**Figure 10. Diode Forward Current**



**Figure 11. Capacitance**

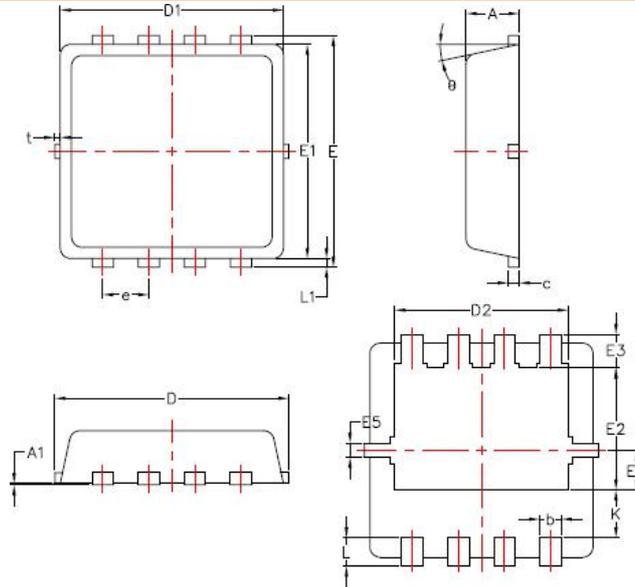


**Figure 12. Gate Charge**



**PACKAGE INFORMATION**

PDFN3X3-8L



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	0.7	0.85
A1	-	0.05
b	0.20	0.40
c	0.10	0.25
D	3.15	3.45
D1	3.00	3.25
D2	2.29	2.65
E	3.15	3.45
E1	2.90	3.20
E2	1.54	1.94
E3	0.28	0.68
E4	0.37	0.77
E5	0.10	0.30
e	0.60	0.70
K	0.59	0.89
L	0.30	0.50
L1	0.06	0.20
T	0	0.13
θ	-	12°